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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I²C, SPI, UART/USART, USB
Peripherals	DMA, I²S, LVD, POR, PWM, WDT
Number of I/O	36
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 16x16b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	48-UFQFN Exposed Pad
Supplier Device Package	48-QFN (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mkl27z256vft4

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2.2 Nonswitching electrical specifications

2.2.1 Voltage and current operating requirements

Table 5. Voltage and current operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	3.6	V	
V_{DDA}	Analog supply voltage	1.71	3.6	V	
$V_{DD} - V_{DDA}$	V_{DD} -to- V_{DDA} differential voltage	-0.1	0.1	V	
$V_{SS} - V_{SSA}$	V_{SS} -to- V_{SSA} differential voltage	-0.1	0.1	V	
V_{IH}	Input high voltage • $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$ • $1.7 \text{ V} \leq V_{DD} \leq 2.7 \text{ V}$	$0.7 \times V_{DD}$ $0.75 \times V_{DD}$	— —	V V	
V_{IL}	Input low voltage • $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$ • $1.7 \text{ V} \leq V_{DD} \leq 2.7 \text{ V}$	— —	$0.35 \times V_{DD}$ $0.3 \times V_{DD}$	V V	
V_{HYS}	Input hysteresis	$0.06 \times V_{DD}$	—	V	
I_{ICIO}	IO pin negative DC injection current — single pin • $V_{IN} < V_{SS} - 0.3 \text{ V}$	-3	—	mA	1
I_{ICcont}	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents of 16 contiguous pins • Negative current injection	-25	—	mA	
V_{ODPU}	Open drain pullup voltage level	V_{DD}	V_{DD}	V	2
V_{RAM}	V_{DD} voltage required to retain RAM	1.2	—	V	

1. All I/O pins are internally clamped to V_{SS} through a ESD protection diode. There is no diode connection to V_{DD} . If V_{IN} greater than V_{IO_MIN} ($= V_{SS} - 0.3 \text{ V}$) is observed, then there is no need to provide current limiting resistors at the pads. If this limit cannot be observed then a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as $R = (V_{IO_MIN} - V_{IN})/I_{ICIO}$.
2. Open drain outputs must be pulled to V_{DD} .

2.2.2 LVD and POR operating requirements

Table 6. V_{DD} supply LVD and POR operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR}	Falling V_{DD} POR detect voltage	0.8	1.1	1.5	V	—

Table continues on the next page...

Table 6. V_{DD} supply LVD and POR operating requirements (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V _{LVDH}	Falling low-voltage detect threshold — high range (LVDV = 01)	2.48	2.56	2.64	V	—
V _{LVW1H}	Low-voltage warning thresholds — high range • Level 1 falling (LVWV = 00)	2.62	2.70	2.78	V	1
V _{LVW2H}	• Level 2 falling (LVWV = 01)	2.72	2.80	2.88	V	
V _{LVW3H}	• Level 3 falling (LVWV = 10)	2.82	2.90	2.98	V	
V _{LVW4H}	• Level 4 falling (LVWV = 11)	2.92	3.00	3.08	V	
V _{HYSH}	Low-voltage inhibit reset/recover hysteresis — high range	—	±60	—	mV	—
V _{LVDL}	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	—
V _{LVW1L}	Low-voltage warning thresholds — low range • Level 1 falling (LVWV = 00)	1.74	1.80	1.86	V	1
V _{LVW2L}	• Level 2 falling (LVWV = 01)	1.84	1.90	1.96	V	
V _{LVW3L}	• Level 3 falling (LVWV = 10)	1.94	2.00	2.06	V	
V _{LVW4L}	• Level 4 falling (LVWV = 11)	2.04	2.10	2.16	V	
V _{HYSL}	Low-voltage inhibit reset/recover hysteresis — low range	—	±40	—	mV	—
V _{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	—
t _{LPO}	Internal low power oscillator period — factory trimmed	900	1000	1100	μs	—

1. Rising thresholds are falling threshold + hysteresis voltage

2.2.3 Voltage and current operating behaviors

Table 7. Voltage and current operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V _{OH}	Output high voltage — normal drive pad • 2.7 V ≤ V _{DD} ≤ 3.6 V, I _{OH} = -5 mA • 1.71 V ≤ V _{DD} ≤ 2.7 V, I _{OH} = -1.5 mA	V _{DD} - 0.5	—	V	1
V _{OH}	Output high voltage — high drive pad • 2.7 V ≤ V _{DD} ≤ 3.6 V, I _{OH} = -18 mA • 1.71 V ≤ V _{DD} ≤ 2.7 V, I _{OH} = -6 mA	V _{DD} - 0.5	—	V	1
I _{OHT}	Output high current total for all ports	—	100	mA	
V _{OL}	Output low voltage — normal drive pad	—	0.5	V	1

Table continues on the next page...

Table 9. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	disable, 125 kHz core / 31.25 kHz flash, $V_{DD} = 3.0\text{ V}$ • at 25 °C	—	50	131	µA	
I_{DD_VLPR}	Very-low-power run mode current—2 MHz LIRC mode, While(1) loop in SRAM all peripheral clock enable, 2 MHz core / 0.5 MHz flash, $V_{DD} = 3.0\text{ V}$ • at 25 °C	—	208	289	µA	
I_{DD_WAIT}	Wait mode current—core disabled, 48 MHz system/24 MHz bus, flash disabled (flash doze enabled), all peripheral clocks disabled, MCG_Lite under HIRC mode, $V_{DD} = 3.0\text{ V}$	—	1.81	1.89	mA	
I_{DD_WAIT}	Wait mode current—core disabled, 24 MHz system/12 MHz bus, flash disabled (flash doze enabled), all peripheral clocks disabled, MCG_Lite under HIRC mode, $V_{DD} = 3.0\text{ V}$	—	1.22	1.39	mA	
I_{DD_VLPW}	Very-low-power wait mode current, core disabled, 4 MHz system/ 1 MHz bus and flash, all peripheral clocks disabled, $V_{DD} = 3.0\text{ V}$	—	172	182	µA	
I_{DD_VLPW}	Very-low-power wait mode current, core disabled, 2 MHz system/ 0.5 MHz bus and flash, all peripheral clocks disabled, $V_{DD} = 3.0\text{ V}$	—	69	76	µA	
I_{DD_VLPW}	Very-low-power wait mode current, core disabled, 125 kHz system/ 31.25 kHz bus and flash, all peripheral clocks disabled, $V_{DD} = 3.0\text{ V}$	—	36	40	µA	
I_{DD_PSTOP2}	Partial Stop 2, core and system clock disabled, 12 MHz bus and flash, $V_{DD} = 3.0\text{ V}$	—	1.81	2.06	mA	
I_{DD_PSTOP2}	Partial Stop 2, core and system clock disabled, flash doze enabled, 12 MHz bus, $V_{DD} = 3.0\text{ V}$	—	1.00	1.25	mA	
I_{DD_STOP}	Stop mode current at 3.0 V • at 25 °C and below • at 50 °C • at 85 °C • at 105 °C	— — — —	161.93 181.45 236.29 390.33	171.82 191.96 271.17 465.58	µA	
I_{DD_VLPS}	Very-low-power stop mode current at 3.0 V • at 25 °C and below • at 50 °C • at 85 °C • at 105 °C	— — — —	3.31 10.43 34.14 104.38	5.14 17.68 61.06 164.44	µA	
I_{DD_VLPS}	Very-low-power stop mode current at 1.8 V • at 25 °C and below	—	3.21	5.22		

Table continues on the next page...

Table 20. Oscillator DC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	<ul style="list-style-type: none"> • 24 MHz • 32 MHz 	—	1.5	—	mA	
I _{DDOSC}	Supply current — high gain mode (HGO=1) <ul style="list-style-type: none"> • 32 kHz • 4 MHz • 8 MHz (RANGE=01) • 16 MHz • 24 MHz • 32 MHz 	—	25	—	µA	¹
		—	400	—	µA	
		—	500	—	µA	
		—	2.5	—	mA	
		—	3	—	mA	
		—	4	—	mA	
C _x	EXTAL load capacitance	—	—	—		^{2, 3}
C _y	XTAL load capacitance	—	—	—		^{2, 3}
R _F	Feedback resistor — low-frequency, low-power mode (HGO=0)	—	—	—	MΩ	^{2, 4}
	Feedback resistor — low-frequency, high-gain mode (HGO=1)	—	10	—	MΩ	
	Feedback resistor — high-frequency, low-power mode (HGO=0)	—	—	—	MΩ	
	Feedback resistor — high-frequency, high-gain mode (HGO=1)	—	1	—	MΩ	
R _S	Series resistor — low-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — low-frequency, high-gain mode (HGO=1)	—	200	—	kΩ	
	Series resistor — high-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — high-frequency, high-gain mode (HGO=1)	—	0	—	kΩ	
V _{pp} ⁵	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, high-gain mode (HGO=1)	—	V _{DD}	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, high-gain mode (HGO=1)	—	V _{DD}	—	V	

1. V_{DD}=3.3 V, Temperature =25 °C

2. See crystal or resonator manufacturer's recommendation

3. C_x, C_y can be provided by using the integrated capacitors when the low frequency oscillator (RANGE = 00) is used. For all other cases external capacitors must be used.
4. When low power mode is selected, R_F is integrated and must not be attached externally.
5. The EXTAL and XTAL pins should only be connected to required oscillator components and must not be connected to any other devices.

3.3.2.2 Oscillator frequency specifications

Table 21. Oscillator frequency specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{osc_lo}	Oscillator crystal or resonator frequency — low-frequency mode (MCG_C2[RANGE]=00)	32	—	40	kHz	
$f_{osc_hi_1}$	Oscillator crystal or resonator frequency — high-frequency mode (low range) (MCG_C2[RANGE]=01)	3	—	8	MHz	
$f_{osc_hi_2}$	Oscillator crystal or resonator frequency — high frequency mode (high range) (MCG_C2[RANGE]=1x)	8	—	32	MHz	
f_{ec_extal}	Input clock frequency (external clock mode)	—	—	48	MHz	1, 2
t_{dc_extal}	Input clock duty cycle (external clock mode)	40	50	60	%	
t_{cst}	Crystal startup time — 32 kHz low-frequency, low-power mode (HGO=0)	—	750	—	ms	3, 4
	Crystal startup time — 32 kHz low-frequency, high-gain mode (HGO=1)	—	250	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), low-power mode (HGO=0)	—	0.6	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), high-gain mode (HGO=1)	—	1	—	ms	

1. Other frequency limits may apply when external clock is being used as a reference for the FLL
2. When transitioning from FEI or FBI to FBE mode, restrict the frequency of the input clock so that, when it is divided by FRDIV, it remains within the limits of the DCO input clock frequency.
3. Proper PC board layout procedures must be followed to achieve specifications.
4. Crystal startup time is defined as the time between the oscillator being enabled and the OSCINIT bit in the MCG_S register being set.

3.4 Memories and memory interfaces

3.4.1 Flash electrical specifications

This section describes the electrical characteristics of the flash memory module.

3.4.1.3 Flash high voltage current behaviors

Table 24. Flash high voltage current behaviors

Symbol	Description	Min.	Typ.	Max.	Unit
I _{DD_PGM}	Average current adder during high voltage flash programming operation	—	2.5	6.0	mA
I _{DD_ERS}	Average current adder during high voltage flash erase operation	—	1.5	4.0	mA

3.4.1.4 Reliability specifications

Table 25. NVM reliability specifications

Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes
Program Flash						
t _{nvmretp10k}	Data retention after up to 10 K cycles	5	50	—	years	—
t _{nvmretp1k}	Data retention after up to 1 K cycles	20	100	—	years	—
n _{nvmcyccp}	Cycling endurance	10 K	50 K	—	cycles	²

1. Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25 °C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.
2. Cycling endurance represents number of program/erase cycles at $-40^{\circ}\text{C} \leq T_j \leq 125^{\circ}\text{C}$.

3.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

3.6 Analog

3.6.1 ADC electrical specifications

Using differential inputs can achieve better system accuracy than using single-end inputs.

2. Typical values assume $V_{DDA} = 3.0$ V, Temp = 25 °C, $f_{ADCK} = 2.0$ MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
3. The ADC supply current depends on the ADC conversion clock speed, conversion rate and ADC_CFG1[ADLPC] (low power). For lowest power operation, ADC_CFG1[ADLPC] must be set, the ADC_CFG2[ADHSC] bit must be clear with 1 MHz ADC conversion clock speed.
4. 1 LSB = $(V_{REFH} - V_{REFL})/2^N$
5. ADC conversion clock < 16 MHz, Max hardware averaging (AVGE = %1, AVGS = %11)
6. Input data is 100 Hz sine wave. ADC conversion clock < 12 MHz.
7. Input data is 1 kHz sine wave. ADC conversion clock < 12 MHz.
8. ADC conversion clock < 3 MHz

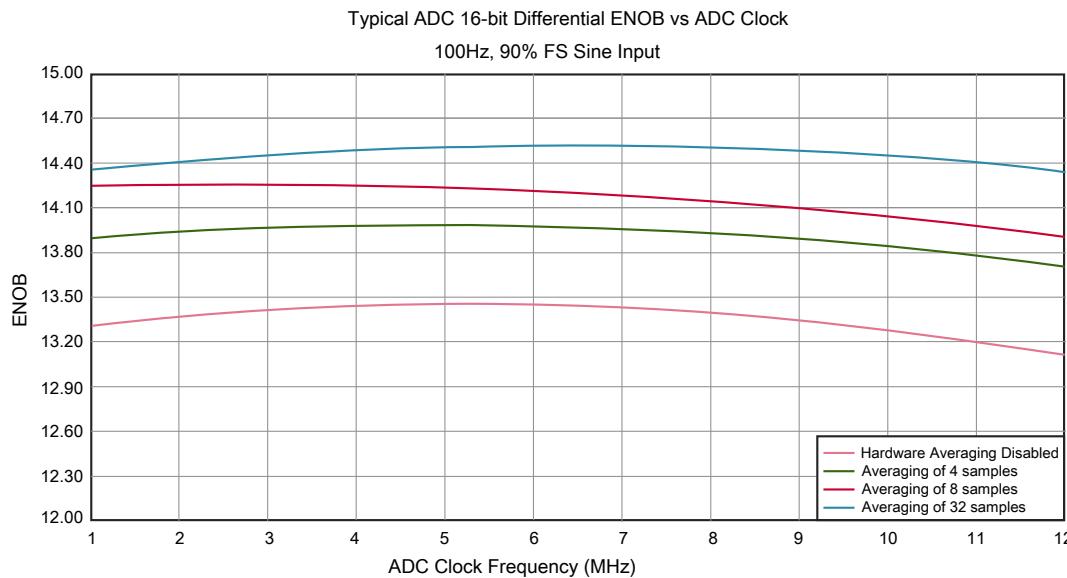


Figure 8. Typical ENOB vs. ADC_CLK for 16-bit differential mode

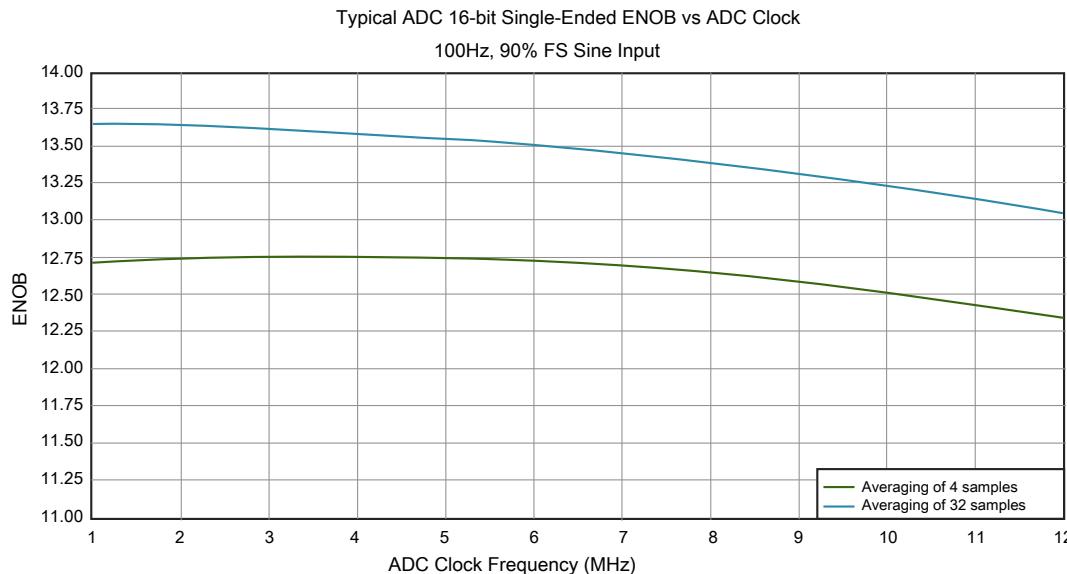


Figure 9. Typical ENOB vs. ADC_CLK for 16-bit single-ended mode

3.6.2 Voltage reference electrical specifications

Table 28. VREF full-range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V _{DDA}	Supply voltage		3.6	V	—
T _A	Temperature	Operating temperature range of the device		°C	—
C _L	Output load capacitance	100		nF	1, 2

1. C_L must be connected to VREF_OUT if the VREF_OUT functionality is being used for either an internal or external reference.
2. The load capacitance should not exceed +/-25% of the nominal specified C_L value over the operating temperature range of the device.

Table 29 is tested under the condition of setting VREF_TRM[CHOPEN], VREF_SC[REGEN] and VREF_SC[ICOMPEN] bits to 1.

Table 29. VREF full-range operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V _{out}	Voltage reference output with factory trim at nominal V _{DDA} and temperature=25°C	1.1915	1.195	1.1977	V	1
V _{out}	Voltage reference output — factory trim	1.1584	—	1.2376	V	1
V _{out}	Voltage reference output — user trim	1.193	—	1.197	V	1
V _{step}	Voltage reference trim step	—	0.5	—	mV	1
V _{tdrift}	Temperature drift (Vmax -Vmin across the full temperature range: 0 to 70°C)	—	—	50	mV	1
I _{bg}	Bandgap only current	—	—	80	µA	1
I _{lp}	Low-power buffer current	—	—	360	uA	1
I _{hp}	High-power buffer current	—	—	1	mA	1
ΔV _{LOAD}	Load regulation • current = ± 1.0 mA	—	200	—	µV	1, 2
T _{stup}	Buffer startup time	—	—	100	µs	—
T _{chop_osc_st up}	Internal bandgap start-up delay with chop oscillator enabled	—	—	35	ms	—
V _{vdrift}	Voltage drift (Vmax -Vmin across the full voltage range)	—	2	—	mV	1

1. See the chip's Reference Manual for the appropriate settings of the VREF Status and Control register.
2. Load regulation voltage is the difference between the VREF_OUT voltage with no load vs. voltage with defined load

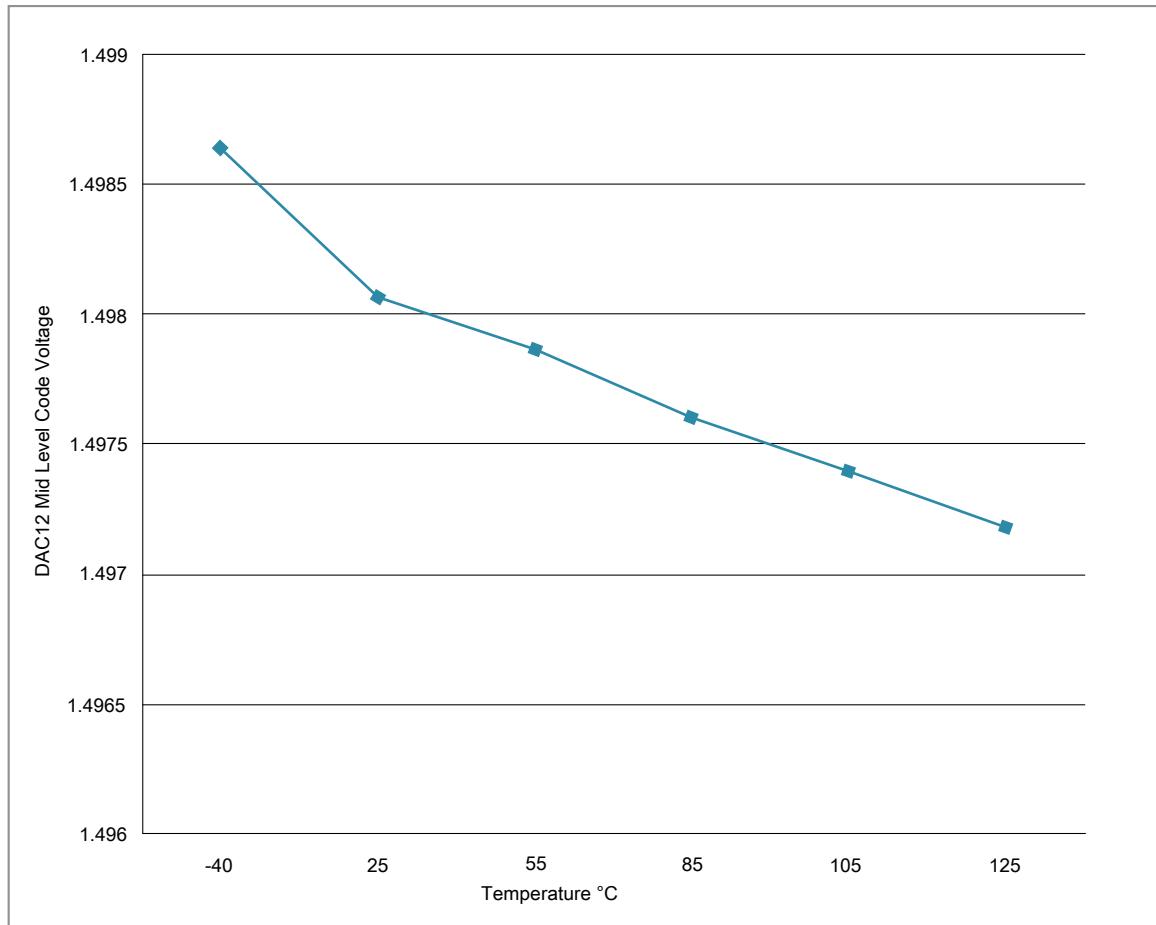


Figure 13. Offset at half scale vs. temperature

3.7 Timers

See [General switching specifications](#).

3.8 Communication interfaces

3.8.1 USB electrical specifications

The USB electricals for the USB On-the-Go module conform to the standards documented by the Universal Serial Bus Implementers Forum. For the most up-to-date standards, visit usb.org .

NOTE

The IRC48M do not meet the USB jitter specifications for certification for Host mode operation.

This device cannot support Host mode operation.

3.8.2 USB VREG electrical specifications

Table 35. USB VREG electrical specifications

Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes
VREGIN	Input supply voltage	2.7	—	5.5	V	
I _{DDon}	Quiescent current — Run mode, load current equal zero, input supply (VREGIN) > 3.6 V	—	125	186	µA	
I _{Ddstby}	Quiescent current — Standby mode, load current equal zero	—	1.1	10	µA	
I _{DDoff}	Quiescent current — Shutdown mode <ul style="list-style-type: none"> • VREGIN = 5.0 V and temperature=25 °C • Across operating voltage and temperature 	—	650	—	nA	
—	—	—	—	4	µA	
I _{LOADrun}	Maximum load current — Run mode	—	—	120	mA	
I _{LOADdstby}	Maximum load current — Standby mode	—	—	1	mA	
V _{Reg33out}	Regulator output voltage — Input supply (VREGIN) > 3.6 V <ul style="list-style-type: none"> • Run mode • Standby mode 	3	3.3	3.6	V	
		2.1	2.8	3.6	V	
V _{Reg33out}	Regulator output voltage — Input supply (VREGIN) < 3.6 V, pass-through mode	2.1	—	3.6	V	²
C _{OUT}	External output capacitor	1.76	2.2	8.16	µF	
ESR	External output capacitor equivalent series resistance	1	—	100	mΩ	
I _{LIM}	Short circuit current	—	290	—	mA	

1. Typical values assume VREGIN = 5.0 V, Temp = 25 °C unless otherwise stated.

2. Operating in pass-through mode: regulator output voltage equal to the input voltage minus a drop proportional to I_{Load}.

3.8.3 SPI switching specifications

The Serial Peripheral Interface (SPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The following tables provide timing characteristics for classic SPI timing modes. See the SPI chapter of the chip's Reference Manual for information about the modified transfer formats used for communicating with slower peripheral devices.

All timing is shown with respect to 20% V_{DD} and 80% V_{DD} thresholds, unless noted, as well as input signal transitions of 3 ns and a 30 pF maximum load on all SPI pins.

Table 36. SPI master mode timing on slew rate disabled pads

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f_{op}	Frequency of operation	$f_{periph}/2048$	$f_{periph}/2$	Hz	1
2	t_{SPSCK}	SPSCK period	$2 \times t_{periph}$	$2048 \times t_{periph}$	ns	2
3	t_{Lead}	Enable lead time	1/2	—	t_{SPSCK}	—
4	t_{Lag}	Enable lag time	1/2	—	t_{SPSCK}	—
5	t_{WSPSCK}	Clock (SPSCK) high or low time	$t_{periph} - 30$	$1024 \times t_{periph}$	ns	—
6	t_{SU}	Data setup time (inputs)	18	—	ns	—
7	t_{HI}	Data hold time (inputs)	0	—	ns	—
8	t_v	Data valid (after SPSCK edge)	—	15	ns	—
9	t_{HO}	Data hold time (outputs)	0	—	ns	—
10	t_{RI}	Rise time input	—	$t_{periph} - 25$	ns	—
	t_{FI}	Fall time input				
11	t_{RO}	Rise time output	—	25	ns	—
	t_{FO}	Fall time output				

1. For SPI0 f_{periph} is the bus clock (f_{BUS}). For SPI1 f_{periph} is the system clock (f_{SYS}).

2. $t_{periph} = 1/f_{periph}$

Table 37. SPI master mode timing on slew rate enabled pads

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f_{op}	Frequency of operation	$f_{periph}/2048$	$f_{periph}/2$	Hz	1
2	t_{SPSCK}	SPSCK period	$2 \times t_{periph}$	$2048 \times t_{periph}$	ns	2
3	t_{Lead}	Enable lead time	1/2	—	t_{SPSCK}	—
4	t_{Lag}	Enable lag time	1/2	—	t_{SPSCK}	—
5	t_{WSPSCK}	Clock (SPSCK) high or low time	$t_{periph} - 30$	$1024 \times t_{periph}$	ns	—
6	t_{SU}	Data setup time (inputs)	96	—	ns	—
7	t_{HI}	Data hold time (inputs)	0	—	ns	—

Table continues on the next page...

Table 39. SPI slave mode timing on slew rate enabled pads

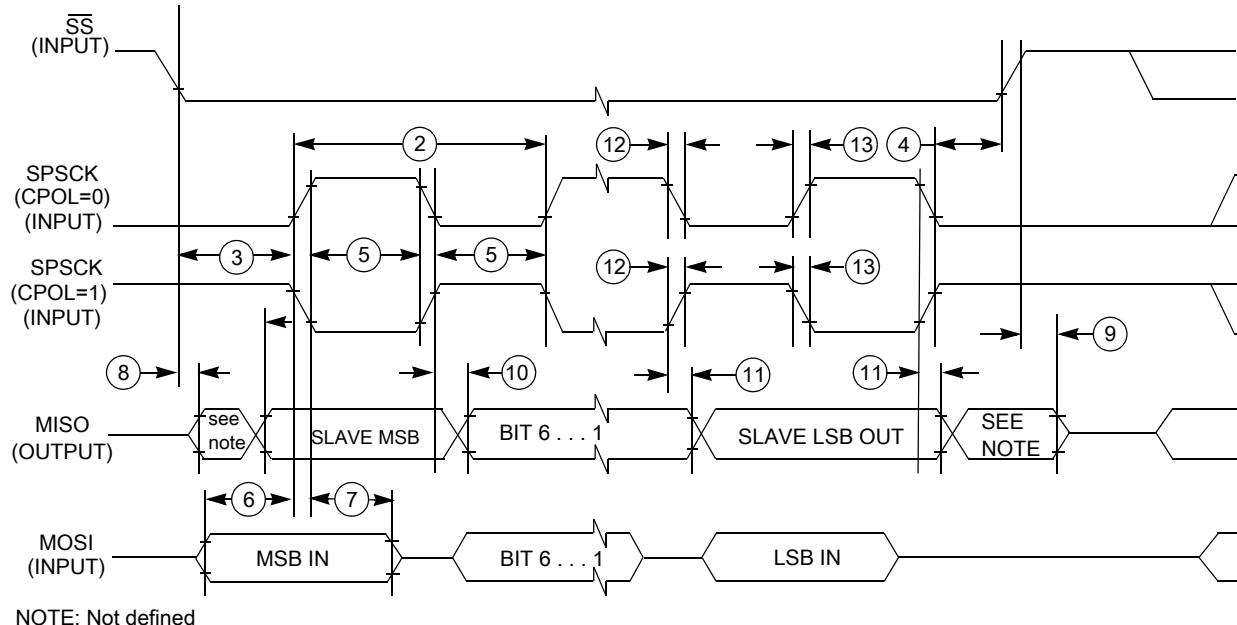
Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f_{op}	Frequency of operation	0	$f_{periph}/4$	Hz	1
2	t_{SPSCK}	SPSCK period	$4 \times t_{periph}$	—	ns	2
3	t_{Lead}	Enable lead time	1	—	t_{periph}	—
4	t_{Lag}	Enable lag time	1	—	t_{periph}	—
5	t_{WPSCK}	Clock (SPSCK) high or low time	$t_{periph} - 30$	—	ns	—
6	t_{SU}	Data setup time (inputs)	2	—	ns	—
7	t_{HI}	Data hold time (inputs)	7	—	ns	—
8	t_a	Slave access time	—	t_{periph}	ns	3
9	t_{dis}	Slave MISO disable time	—	t_{periph}	ns	4
10	t_v	Data valid (after SPSCK edge)	—	122	ns	—
11	t_{HO}	Data hold time (outputs)	0	—	ns	—
12	t_{RI}	Rise time input	—	$t_{periph} - 25$	ns	—
	t_{FI}	Fall time input				
13	t_{RO}	Rise time output	—	36	ns	—
	t_{FO}	Fall time output				

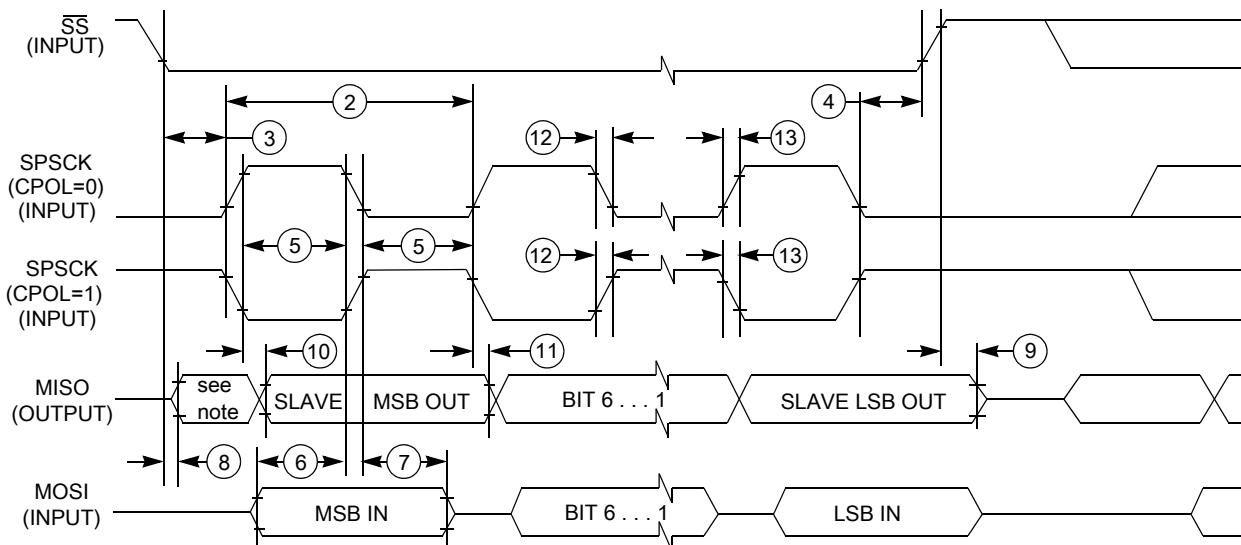
1. For SPI0 f_{periph} is the bus clock (f_{BUS}). For SPI1 f_{periph} is the system clock (f_{sys}).

2. $t_{periph} = 1/f_{periph}$

3. Time to data active from high-impedance state

4. Hold time to high-impedance state

**Figure 16. SPI slave mode timing (CPHA = 0)**



NOTE: Not defined

Figure 17. SPI slave mode timing (CPHA = 1)

3.8.4 I²C

3.8.4.1 Inter-Integrated Circuit Interface (I²C) timing

Table 40. I²C timing

Characteristic	Symbol	Standard Mode		Fast Mode		Unit
		Minimum	Maximum	Minimum	Maximum	
SCL Clock Frequency	f _{SCL}	0	100	0	400 ¹	kHz
Hold time (repeated) START condition. After this period, the first clock pulse is generated.	t _{HD; STA}	4	—	0.6	—	μs
LOW period of the SCL clock	t _{LOW}	4.7	—	1.25	—	μs
HIGH period of the SCL clock	t _{HIGH}	4	—	0.6	—	μs
Set-up time for a repeated START condition	t _{SU; STA}	4.7	—	0.6	—	μs
Data hold time for I ² C bus devices	t _{HD; DAT}	0 ²	3.45 ³	0 ⁴	0.9 ²	μs
Data set-up time	t _{SU; DAT}	250 ⁵	—	100 ^{3, 6}	—	ns
Rise time of SDA and SCL signals	t _r	—	1000	20 + 0.1C _b ⁷	300	ns
Fall time of SDA and SCL signals	t _f	—	300	20 + 0.1C _b ⁶	300	ns
Set-up time for STOP condition	t _{SU; STO}	4	—	0.6	—	μs
Bus free time between STOP and START condition	t _{BUF}	4.7	—	1.3	—	μs
Pulse width of spikes that must be suppressed by the input filter	t _{SP}	N/A	N/A	0	50	ns

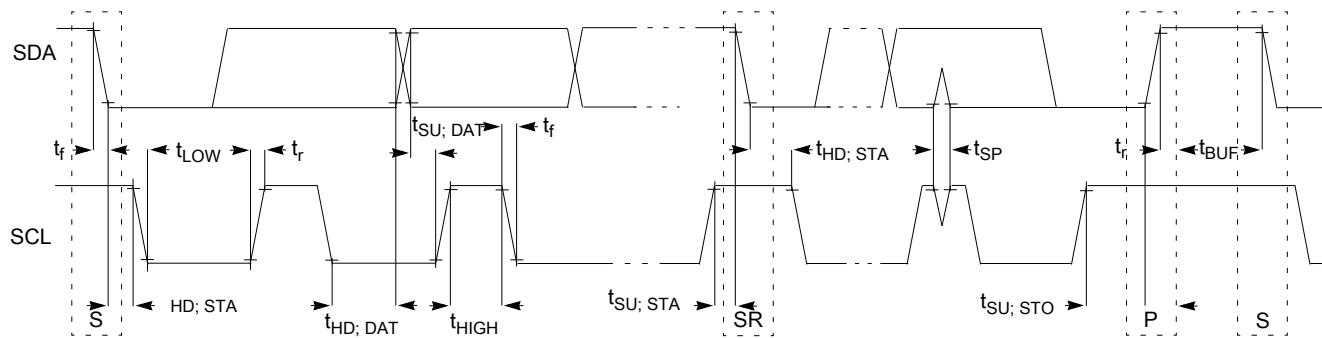


Figure 18. Timing definition for devices on the I²C bus

3.8.5 UART

See [General switching specifications](#).

3.8.6 I2S/SAI switching specifications

This section provides the AC timing for the I2S/SAI module in master mode (clocks are driven) and slave mode (clocks are input). All timing is given for noninverted serial clock polarity (TCR2[BCP] is 0, RCR2[BCP] is 0) and a noninverted frame sync (TCR4[FSP] is 0, RCR4[FSP] is 0). If the polarity of the clock and/or the frame sync have been inverted, all the timing remains valid by inverting the bit clock signal (BCLK) and/or the frame sync (FS) signal shown in the following figures.

3.8.6.1 Normal Run, Wait and Stop mode performance over the full operating voltage range

This section provides the operating performance over the full operating voltage for the device in Normal Run, Wait and Stop modes.

Table 42. I2S/SAI master mode timing

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S1	I2S_MCLK cycle time	40	—	ns
S2	I2S_MCLK (as an input) pulse width high/low	45%	55%	MCLK period
S3	I2S_TX_BCLK/I2S_RX_BCLK cycle time (output)	80	—	ns
S4	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low	45%	55%	BCLK period
S5	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output valid	—	15.5	ns

Table continues on the next page...

32 QFN	48 QFN	64 MAP BGA	64 LQFP	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
17	24	H8	32	PTA18	EXTAL0	EXTAL0	PTA18		LPUART1_RX	TPM_CLKIN0			
18	25	G8	33	PTA19	XTAL0	XTAL0	PTA19		LPUART1_TX	TPM_CLKIN1		LPTMR0_ALT1	
19	26	F8	34	PTA20	RESET_b		PTA20						RESET_b
20	27	F7	35	PTB0/ LLWU_P5	ADC0_SE8	ADC0_SE8	PTB0/ LLWU_P5	I2C0_SCL	TPM1_CH0				
21	28	F6	36	PTB1	ADC0_SE9	ADC0_SE9	PTB1	I2C0_SDA	TPM1_CH1				
22	34	C6	44	PTC1/ LLWU_P6/ RTC_CLKIN	ADC0_SE15	ADC0_SE15	PTC1/ LLWU_P6/ RTC_CLKIN	I2C1_SCL		TPM0_CH0		I2S0_TXD0	
23	35	B7	45	PTC2	ADC0_SE11	ADC0_SE11	PTC2	I2C1_SDA		TPM0_CH1		I2S0_TX_FS	
24	36	C8	46	PTC3/ LLWU_P7	DISABLED		PTC3/ LLWU_P7	SPI1_SCK	LPUART1_RX	TPM0_CH2	CLKOUT	I2S0_TX_BCLK	
25	37	B8	49	PTC4/ LLWU_P8	DISABLED		PTC4/ LLWU_P8	SPI0_SS	LPUART1_TX	TPM0_CH3	I2S0_MCLK		
26	38	A8	50	PTC5/ LLWU_P9	DISABLED		PTC5/ LLWU_P9	SPI0_SCK	LPTMR0_ALT2	I2S0_RXD0		CMP0_OUT	
27	39	A7	51	PTC6/ LLWU_P10	CMP0_IN0	CMP0_IN0	PTC6/ LLWU_P10	SPI0_MOSI	EXTRG_IN	I2S0_RX_BCLK	SPI0_MISO	I2S0_MCLK	
28	40	B6	52	PTC7	CMP0_IN1	CMP0_IN1	PTC7	SPI0_MISO	audioUSB_SOF_OUT	I2S0_RX_FS	SPI0_MOSI		
29	45	A3	61	PTD4/ LLWU_P14	DISABLED		PTD4/ LLWU_P14	SPI1_SS	UART2_RX	TPM0_CH4		FXIO0_D4	
30	46	C1	62	PTD5	ADC0_SE6b	ADC0_SE6b	PTD5	SPI1_SCK	UART2_TX	TPM0_CH5		FXIO0_D5	
31	47	B2	63	PTD6/ LLWU_P15	ADC0_SE7b	ADC0_SE7b	PTD6/ LLWU_P15	SPI1_MOSI	LPUART0_RX		SPI1_MISO	FXIO0_D6	
32	48	A2	64	PTD7	DISABLED		PTD7	SPI1_MISO	LPUART0_TX		SPI1_MOSI	FXIO0_D7	

5.2 KL27 Family Pinouts

Figure below shows the 32 QFN pinouts:

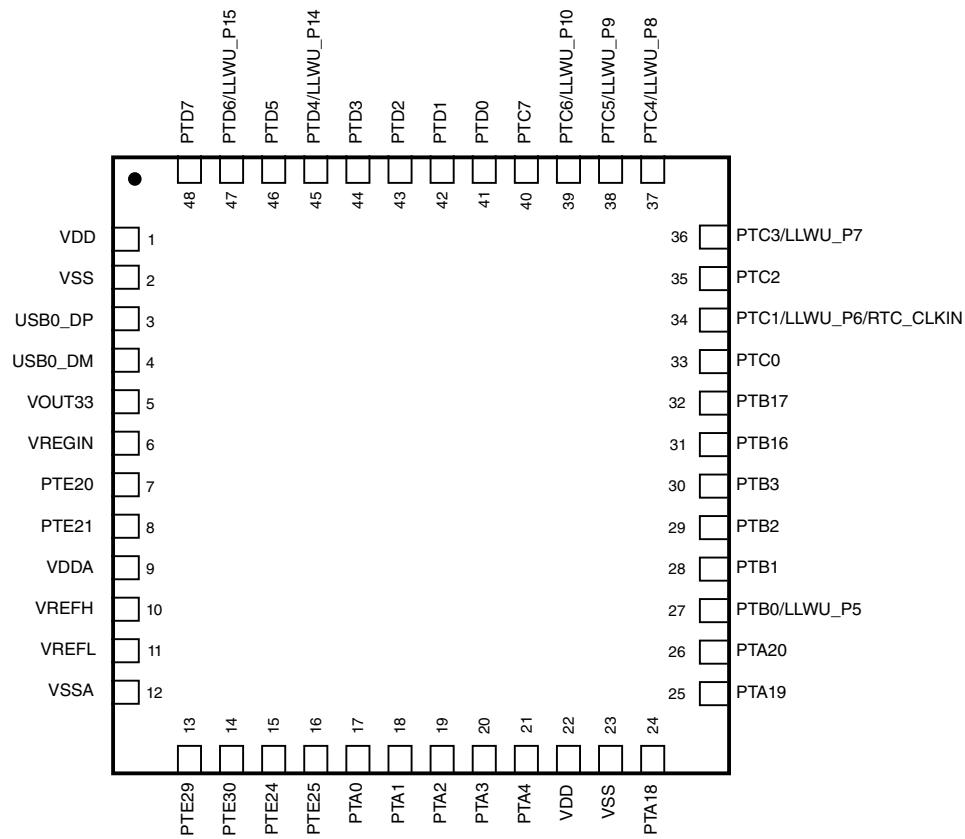


Figure 24. 48 QFN Pinout diagram

Figure below shows the 64 LQFP pinouts:

7.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

7.2 Format

Part numbers for this device have the following format:

Q KL## A FFF R T PP CC N

7.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Table 46. Part number fields descriptions

Field	Description	Values
Q	Qualification status	<ul style="list-style-type: none">• M = Fully qualified, general market flow• P = Prequalification
KL##	Kinetis family	<ul style="list-style-type: none">• KL27
A	Key attribute	<ul style="list-style-type: none">• Z = Cortex-M0+
FFF	Program flash memory size	
R	Silicon revision	<ul style="list-style-type: none">• (Blank) = Main• A = Revision after main
T	Temperature range (°C)	<ul style="list-style-type: none">• V = -40 to 105
PP	Package identifier	<ul style="list-style-type: none">• FM = 32 QFN (5 mm x 5 mm)• FT = 48 QFN (7 mm x 7 mm)• LH = 64 LQFP (10 mm x 10 mm)• MP = 64 MAPBGA (5 mm x 5 mm)
CC	Maximum CPU frequency (MHz)	<ul style="list-style-type: none">• 4 = 48 MHz
N	Packaging type	<ul style="list-style-type: none">• R = Tape and reel

7.4 Example

This is an example part number:

MKL27Z256VFT4

Table 47. Revision History (continued)

Rev. No.	Date	Substantial Changes
		<ul style="list-style-type: none"> • Updated Related Resources table to include Chip Errata resource name and Package Drawing part numbers in the respective rows. Also updated Product Brief resource references. • Updated Table 7. Voltage and current operating behaviors. <ul style="list-style-type: none"> • Specified correct max. value for I_{IN}. • Updated Table - 9 Power consumption operating behaviors. <ul style="list-style-type: none"> • Rows added for IDD for reset pin hold low ($I_{DD_RESET_LOW}$) at 1.7V and 3V. • Measurement unit updated for I_{DD_VLLS1} from nA to μA. • Footnote 1 was moved in the beginning of the table as text. • Added Table - 11 EMC radiated emissions operating behaviors for 64-pin LQFP package under section 2.2.6. • Updated Table - 18 (IRC48M specification) and Table - 19 (IRC8M/2M specification) under section 3.3.1 - 'MCG-Lite specifications'. <ul style="list-style-type: none"> • Removed supply voltage (V_{DD}), temperature range (T), untrimmed (f_{IRC_UT}), trim function (Δf_{IRC_C}, Δf_{IRC_F}) data from Table - 18 (IRC48M specification). • Removed supply voltage (V_{DD}), temperature range (T) data from Table - 19 (IRC8M/2M specification). • Added Figure 6. IRC8M Frequency Drift vs Temperature curve after Table - 19 (IRC8M/2M specification). • Updated Table 29. VREF full-range operating behaviors. <ul style="list-style-type: none"> • Removed A_c(Aging coefficient) row. • Added $T_{chop_osc_stup}$ parameter. • Added tables: "I²C timing" and "I²C 1Mbit/s timing" under section - I²C. • Added VREF specifications (V_{REFH} and V_{REFL}) to Table 26. 16-bit ADC operating conditions. • Removed note: "This device does not have the USB_CLKIN signal available."
5	12 August 2015	<ul style="list-style-type: none"> • In Table 9. Power consumption operating behaviors: <ul style="list-style-type: none"> • Updated Max. values of I_{DD_WAIT}, I_{DD_VLPW}, I_{DD_STOP}, I_{DD_VLPS}, I_{DD_LLS}, I_{DD_VLLS3}, I_{DD_VLLS1}, I_{DD_VLLS0}. • Modified unit of I_{DD_VLLS0} from nA to μA. • Removed $I_{DD_RESET_LOW}$ information. • In Table 13. Device clock specifications, added a footnote for normal run mode. • In Table 15. Thermal operating requirements, modified the footnote for Ambient temperature. • In Table 18. IRC48M specification, removed f_{IRC_T} data and added $\Delta f_{irc48m_of_lv}$ and $\Delta f_{irc48m_of_hv}$ specifications. • In Table 26. 16-bit ADC operating conditions, updated Max. value of f_{ADCK} and C_{rate}.

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